IN THE CLAIMS

1-10. (Canceled)

11. (Currently amended) A transceiver apparatus comprising:

[[a]] an RF oscillator apparatus having a cavity resonator and a conductor plate which supports a microwave monolithic integrated circuit chip electromagnetically coupled to the cavity resonator, a resonance frequency of the cavity resonator being set in advance;

a receiving section which makes [[a]] an RF signal generated from the RF oscillator apparatus a local oscillation signal of a mixer; and

a transmitting section having an amplifier for amplifying power.

12. (Currently amended) A ~~RF oscillator~~ transceiver apparatus according to claim [[2]] 28, wherein a chip capacitor connected to the microwave monolithic integrated circuit chip is loaded on the conductor plate.

13. (Currently amended) A ~~RF oscillator~~ transceiver apparatus according to claim [[3]] 29, wherein a chip

capacitor connected to the microwave monolithic integrated circuit chip is loaded on the conductor plate.

14. (Currently amended) A ~~RF oscillator~~ transceiver apparatus according to claim [[4]] 30, wherein a chip capacitor connected to the microwave monolithic integrated circuit chip is loaded on the conductor plate.

15. (Currently amended) A ~~RF oscillator~~ transceiver apparatus according to claim [[5]] 31, wherein a chip capacitor connected to the microwave monolithic integrated circuit chip is loaded on the conductor plate.

16. (Currently amended) A transceiver apparatus according to claim [[8]] 11, wherein such a seal material as to cover an upper portion of the ~~conductive wall~~ cavity resonator is provided.

17. (Currently amended) A transceiver apparatus according to claim [[8]] 11, wherein the receiving section and the amplifier are constituted by microwave monolithic integrated circuit chips.

18. (Canceled)

19. (Original) A transceiver apparatus according to claim 16, wherein the receiving section and the amplifier are constituted by microwave monolithic integrated circuit chips.

20. (Currently amended) A manufacturing process of a transceiver apparatus, the process comprising the steps of:

preparing [[a]] an RF oscillator apparatus whose resonance frequency is set in advance, a first semiconductor chip constituting a receiving section which makes [[a]] an RF signal generated from the RF oscillator apparatus a local oscillation signal of a mixer, and a second semiconductor chip constituting a transmitting section having an amplifier for amplifying power;

fixing the RF oscillator apparatus and the first and second semiconductor chips to a module substrate by an adhesive;

connecting wires of the module substrate to the RF oscillator apparatus and the first and second semiconductor chips by wire bonding, respectively; and

airtightly sealing the RF oscillator apparatus and the first and second semiconductor chips loaded on the module substrate.

21. (Currently amended) A manufacturing process of a transceiver apparatus according to claim 20, wherein the module substrate ~~is used as a module substrate having~~ has a wiring substrate ~~being~~ connected by the wire bonding and a base substrate supporting the wiring substrate.

22. (Currently amended) A manufacturing process of a transceiver apparatus according to claim 20, wherein the RF oscillator apparatus ~~is used as a RF oscillator apparatus having~~ has a dielectric resonator, a conductor plate which supports a microwave monolithic integrated circuit chip electromagnetically coupled to the dielectric resonator, and a conductive wall which determines a resonance frequency of the dielectric resonator.

23. (Original) A manufacturing process of a transceiver apparatus according to claim 20, wherein silver paste is used as the adhesive.

24. (Currently amended) A manufacturing process of a transceiver apparatus according to claim 21, wherein the RF oscillator apparatus ~~is used as a RF oscillator apparatus having~~ has a dielectric resonator, a conductor plate which supports a microwave monolithic integrated circuit chip

electromagnetically coupled to the dielectric resonator, and a conductive wall which determines a resonance frequency of the dielectric resonator.

25. (Original) A manufacturing process of a transceiver apparatus according to claim 21, wherein silver paste is used as the adhesive.

26. (Original) A manufacturing process of a transceiver apparatus according to claim 22, wherein silver paste is used as the adhesive.

27. (Original) A manufacturing process of a transceiver apparatus according to claim 24, wherein silver paste is used as the adhesive.

28. (New) A transceiver apparatus according to claim 11, wherein an air gap is formed between the cavity resonator and the conductor plate.

29. (New) A transceiver apparatus according to claim 11, wherein the cavity resonator is supported by a dielectric supporter such that an air gap is formed between the cavity resonator and the conductor plate.

30. (New) A transceiver apparatus according to claim 29, wherein the dielectric supporter has such a shape as to straddle both sides of the cavity resonator, and is fixed on the conductor plate at both sides of the cavity resonator, and wherein the dielectric supporter and a portion of an upper portion of the cavity resonator are joined to each other.

31. (New) A RF oscillator apparatus according to claim 11, wherein a chip capacitor connected to the microwave monolithic integrated circuit chip is loaded on the conductor plate.